Japan Society of Applied Physics, Advanced Power Semiconductor Subcommittee

10th individual discussion

"Polishing and processing technology for wide bandgap semiconductor substrates"

ÿ Date and time: Thursday, August 4, 2022 13:00-18:00

ÿ Location: Osaka University Graduate School of Medicine and Engineering Tokyo Branch @ Nihonbashi

Nihonbashi Life Science Building **9F , 2-3-11** Nihonbashi Honmachi, Chuo-ku, Tokyo

With the spread of wide bandgap semiconductors, there is a need for larger diameter and lower cost wafers. Among them,

We hope to be able to discuss substrate polishing and processing technology across materials. In this discussion, we will discuss the current state of polishing and processing technology for wide bandgap semiconductor substrates such as SiC, GaN, and Ga2O3, including slicing technology.

Discussions will take place based on issues and the latest trends.

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12:30 Opening

13:00-13:10 Opening remarks, explanation of today's progress

13:10-14:00 Introduction SiC wafer processing

technology for large diameter and low cost Tomohisa Kato (National

Institute of Advanced Industrial Science and Technology))

14:00-14:40 Electrochemical mechanical polishing of SiC using a solid polymer electrolyte-containing pad

Junji Murata (Ritsumeikan University)

14:40-14:50 break

14:50-15:30 Multi-wire discharge slicing technology for next-generation semiconductors

Takashi Yuzawa (Mitsubishi Electric Corporation)

15:30-16:10 Slice of GaN substrate using laser

Atsuyuki Tanaka (Nagoya University)

16:10-16:20 break

16:20-17:00 Improving SiC wafer processing quality using mirror electron microscopy analysis

Takahiro Ikeuchi (Rokko Electronics Co., Ltd.)

17:00-17:55 General discussion based on information provided by

participants 17:55-18:00 Closing remarks

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ÿAbout participation: Discussion on polishing and processing technology for wide bandgap semiconductor substrates based on the latest trends

This is a discussion group where everyone can participate. Due to the nature of the discussion, participants may be asked to give their opinions and comments.

Thank you for your understanding. In addition, when you apply for participation online, we will inform you about the topics that can be discussed and what initiatives we are working on.

Please write as much as possible about the outline of your research and the topics you can provide.

ÿParticipation registration: Please register your participation using the web participation registration system (click here). Deadline: July 27th (Wednesday). Capacity: 25 people. We will stop accepting applications once the capacity is reached, so please apply as soon as possible. We will notify participants at a later date where to download the PDF version of the proceedings. ÿParticipation fee: (tax included) Advanced Power Semiconductor Subcommittee members* 2,000 yen, general public 4,000 yen, students (subcommittee members/general) 1,000 yen ÿInfectious disease countermeasures: Please cooperate in taking your temperature in advance and if you have a fever. Please refrain from participating on the day of the event. Also, please cooperate with the temperature check again at the venue entrance (if your body temperature is 37.5 degrees or higher, you will not be able to participate). At the venue, please disinfect and wear a mask at all times. ÿContact information: Fumimasa Horikiri (SIOX Co., Ltd.) TEL: 0294-42-5025, e-mail: horikirif@sc.sumitomo-chem.co.jp Yasuhisa Sano (Osaka University) TEL: 06-6879-7284, e -mail: sano@prec.eng.osaka-u.ac.jp Kazusato Kojima (National Institute of Advanced Industrial Science and Technology) TEL: 029-861-5728, e-mail: kazu-kojima@aist.go.jp